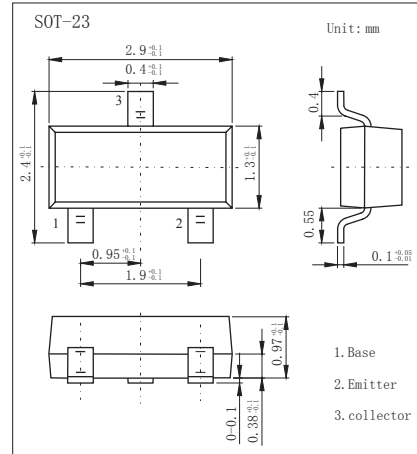


NPN Transistors

MMBTA06

■ Features

- For Switching and Amplifier Applications
- Complementary to MMBTA56



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	80	V
Collector - Emitter Voltage	V_{CE0}	80	
Emitter - Base Voltage	V_{EB0}	4	
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	300	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	416	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 100 \mu\text{A}, I_E = 0$	80			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 1 \text{ mA}, I_B = 0$	80			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}, I_C = 0$	4			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 80 \text{ V}, I_E = 0$			100	nA
Collector- emitter cut-off current	I_{CES}	$V_{CE} = 60 \text{ V}, I_E = 0$			100	
Emitter cut-off current	I_{EBO}	$V_{EB} = 3 \text{ V}, I_C = 0$			100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$			0.25	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$			1.2	
DC current gain	$h_{FE(1)}$	$V_{CE} = 1 \text{ V}, I_C = 10 \text{ mA}$	100		400	
	$h_{FE(2)}$	$V_{CE} = 1 \text{ V}, I_C = 100 \text{ mA}$	100			
Transition frequency	f_T	$V_{CE} = 2 \text{ V}, I_C = 10 \text{ mA}, f = 100 \text{ MHz}$	100			MHz

■ Marking

Marking	1G*
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炬芯微
XUANXINWEI

SMD Type Transistors

NPN Transistors

MMBTA06

Typical Characteristics

